









- Number systems
- Building blocks
- Algorithm representation
- Transformation (retiming, unfolding, folding)
- Mapping algorithms into hardware
- Low power design



































Full Custom vs. Standard Cell

Full custom

- Analog/digital with all customized mask layers and some logic cells
- Full control over sizing and layout
- Standard cell
 - Using pre-designed "cells"
 - Constant-height and regular pin locations























Increasing Performance

| YEAR OF PRODUCTION | 2003 | 20 | 006 | 2009 | 2010 | 2011 | 2015 |
|--|--|---|-----------------------------|------|----------------|-----------------------------------|------|
| Process Technology (nm) | 130 | Ş | 90 | 65 | 45 | 32/28 | 12 |
| Supply Voltage (V) | 1.2 | | 1 | 0.8 | 0.6 | 0.5 | 0.3 |
| Clock Frequency (MHz) | 1000 | 20 | 000 | 2500 | 2900 | 3200 | 4000 |
| Application (maximum required performance) Application (other) | Still Image Processing Web Browser | Real T (N | ime Video Co /IPEG4/CIF) | dec | Real Time Inte | | |
| | Scheduler | TV Telephone (1:1) Voice Recognition (Input) Authentication(Crypto Engine) TV Telephone (>3:1) Voice Recognition (Operation) | | | | one (>3:1) cognition ation) | |
| Processing Performance (GOPS) | 0.3 | 2 | 14 | | 77 | 461 | 2458 |
| Required Average Power (W) | 0.1 | 0.1 | 0.1 | 0.1 | 0.1 | 0.1 | 0.1 |
| Required Standby Power (mW) | 2 | 2 | 2 | | 2 | 2 | 2 |
| Battery Capacity (Wh/Kg) | 120 | 200 | 200 | | 400 | 400 | 400 |







| Little change in basic technology | Energy density of material | KWH/kg |
|--|----------------------------|--------|
| store energy using a chemical reaction | Gasoline | 14 |
| Battery capacity | Lead-Acid | 0.04 |
| years | Li polymer | 0.15 |
| Energy density/ size, safe handling are limiting factor | | 1 |















| Voltage to Presking the Pulse of Seeling | | | | | | | | |
|--|------|-------|-------|---------|--|--|--|--|
| Source: ITRS 2005 | 90nm | 65nm | 45nm | 32/28nm | | | | |
| Device Length (nm) ⊃ | 1x | 0.7x | 0.5x | 0.3x | | | | |
| Delay (ps) C | 1x | 0.7x | 0.5x | 03x | | | | |
| Frequency (GHz) ⇒ | 1x | 1.43x | 2x | 3x | | | | |
| Integration Capacity (BT) ⇒ | 1x | 2x | 4x | 8x | | | | |
| Capacitance (fF) ⊃ | 1x | 0.7x | 0.5x | 0.3x | | | | |
| Die Size (mm²) 🗯 | 1x | 1x | 1x | 1x | | | | |
| Voltage (V) ► | 1x | 0.85x | 0.7x | 0.55x | | | | |
| Power _{Dyn} (W) ►> | 1x | >0.7x | >0.5x | >0.3x | | | | |
| Manufacturing (microcents/T) ⊃ | 1x | 0.35x | 0.12x | 0.08x | | | | |
| V _{TH} (V) ≯ | 1x | .85x | .7x | .55x | | | | |
| I _{OFF} (nA/um) ⇔⇔ | 1x | ~3x | ~9x | ~22x | | | | |
| Power _{Dyn} Density (W/cm²) ⇔ | 1x | 1.43x | 2x | 4x | | | | |
| Power _{Leak} Density (W/cm ²) ⇒ | 1x | ~2.5x | ~6.5x | ~13.5x | | | | |
| Power Density (W/cm ²) ⇒ | 1x | ~2x | ~4x | ~8x | | | | |
| Cu Resistance (Ω) ⇔ | 1x | 2x | 4x | 8x | | | | |
| Interconnect RC Delay (ps) ⇔ | 1x | ~2x | ~5x | ~12x | | | | |
| Packaging (cents/pin) ►> | 1x | 0.86x | 0.73x | 0.58x | | | | |
| Test (nanocents/T) 🗯 | 1x | 1x | 1x | 1x | | | | |









